SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

BST16

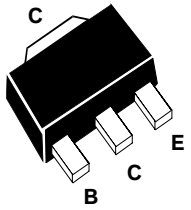
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FEATURES

* High V_{CEO}
* Low saturation voltage

COMPLEMENTARY TYPE – BST39

PARTMARKING DETAIL – BT2



SOT89

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-350	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-4	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-500	mA
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-350			V	I_C=-100µA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300			V	I_C=-1mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4			V	I_E=-100µA
Collector Cut-Off Current	I_{CBO}			-1	µA	V_{CB}=-280V
Collector Cut-Off Current	I_{CEO}			-50	µA	V_{CB}=-250V
Emitter Cut-Off Current	I_{EBO}			-20	µA	V_{EB}=-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			- 2.0 -0.5	V V	I_C=-50mA, I_B=-5mA* I_C=-30mA, I_B=-3mA*
Static Forward Current Transfer Ratio	h_{FE}	30		150		I_C=-50mA, V_{CE}=-10V*
Transition Frequency	f_T	15			MHz	I_C=-10mA, V_{CE}=-10V* f = 30MHz
Output Capacitance	C_{obo}			15	pF	V_{CB}=-10V, f=1MHz

*Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%
For typical characteristics graphs see FMMTA92 datasheet.